

PMBTA44

400 V, 0.3 A NPN high-voltage low V_{CEsat} (BISS) transistor Rev. 01 — 22 February 2008 Product data s

Product data sheet

1. Product profile

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Low current (max. 300 mA)
- High voltage (max. 400 V)
- AEC-Q101 qualified

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	400	V
$I_{\mathbb{C}}$	collector current		-	-	300	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA}$	50	-	200	



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2. Pinning information

Table 2. Pinning

Idbio L.	9	
Pin	Description	Simplified outline Symbol
1	base	
2	emitter	3
3	collector	1 - 2
		sym021

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA44	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMBTA44	W3*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

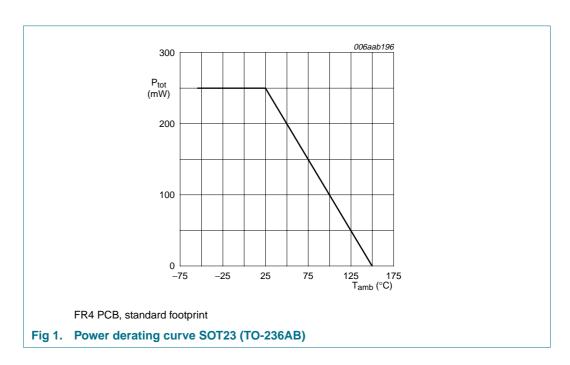
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5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

		• • •	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	500	V
V_{CEO}	collector-emitter voltage	open base	-	400	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	300	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	300	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

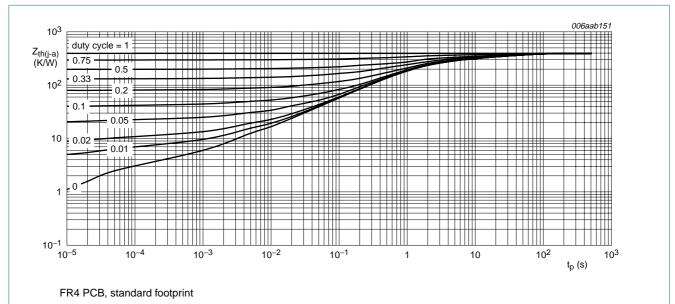


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT23 (TO-236AB)

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7. Characteristics

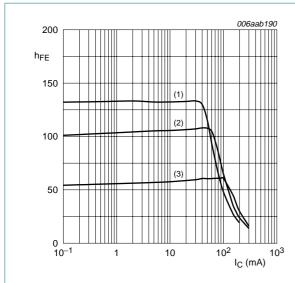
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}		$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
(current	$V_{CB} = 320 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$		-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V					
		I _C = 10 mA		50	-	200	
		$I_C = 50 \text{ mA}$	<u>[1]</u>	45	-	-	
		I _C = 100 mA	<u>[1]</u>	40	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1 \text{ mA}; I_B = 0.1 \text{ mA}$		-	-	400	mV
		$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$		-	-	500	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}$	[1]	-	-	750	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 1 \text{ mA}$	[1]	-	-	850	mV
f _T	transition frequency	$V_{CE} = 10 \text{ V}; I_E = 10 \text{ mA};$ f = 100 MHz		20	-	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V; } I_E = i_e = 0 \text{ A;}$ f = 1 MHz		-	-	7	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$		-	-	180	pF

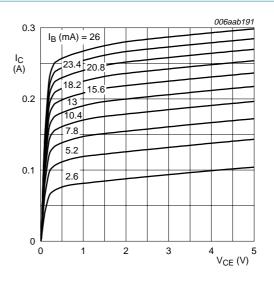
^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

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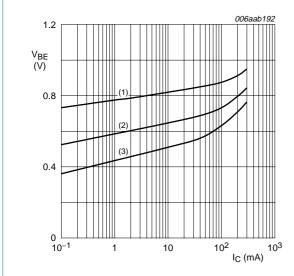
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

Fig 4. Collector current as a function of collector-emitter voltage; typical values



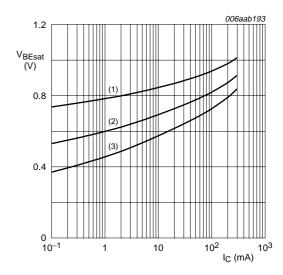
V_{CE} = 10 V

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$

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(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values



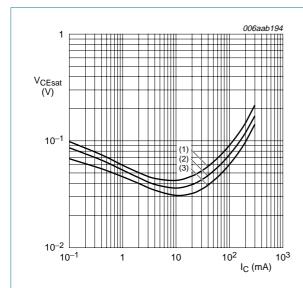
 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55$ °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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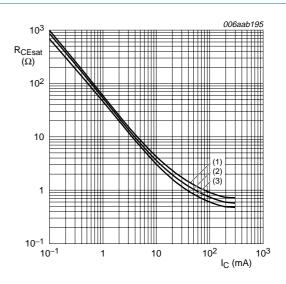
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$$I_{\rm C}/I_{\rm B}=5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \,^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 8. Collector-emitter saturation resistance as a function of collector current; typical values

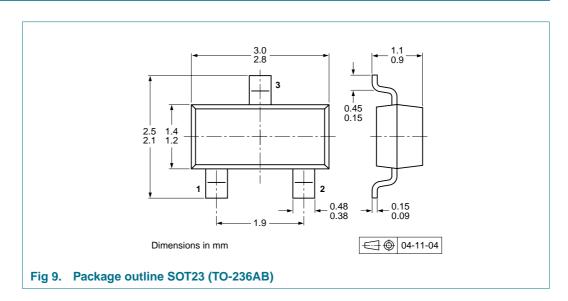
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8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

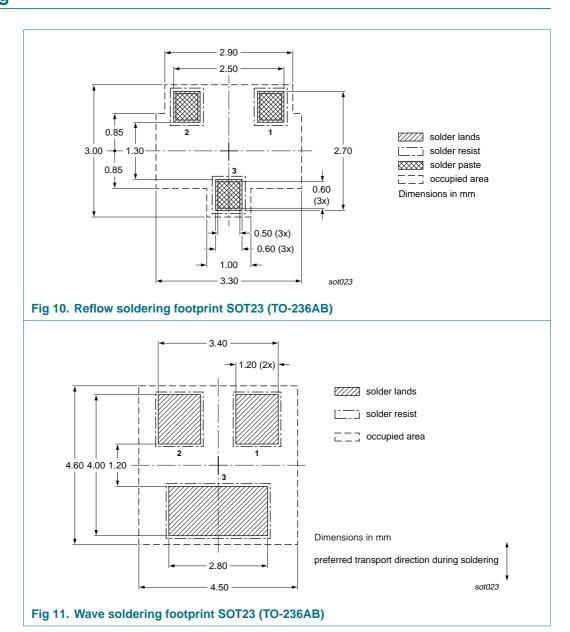
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description Packing (uantity
			3000	10000
PMBTA44	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA44_1	20080222	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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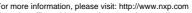
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